



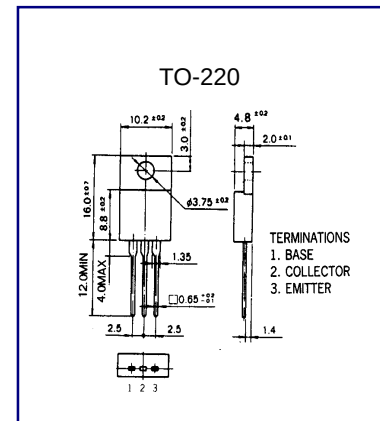
2SB825

PNP EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY POWER AMPLIFIER

ABSOLUTE MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-50	V
Collector-Emitter Voltage	V_{CE0}	-60	V
Emitter-Base voltage	V_{EB0}	-5	V
Collector Current (DC)	I_C	-7	A
Collector Dissipation ($T_c=25^{\circ}\text{C}$)	P_C	40	W
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-50~150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = -50\text{V}, I_E = 0$			-10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			10	μA
DC Current Gain	h_{FE1}	$V_{CE} = -2\text{V}, I_C = -1.0\text{A}$	100			
Collector- Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -4\text{A}, I_B = -0.4\text{A}$			-0.4	V
Current Gain Bandwidth Product	f_T	$V_{CE} = -2\text{V}, I_C = -0.5\text{A}$		8		MHZ